

1      ABSTRACT OF THE DISCLOSURE

2      In one implementation, first and second layers are formed over  
3      a substrate. One of the layers has a higher oxidation rate than the  
4      other when exposed to an oxidizing atmosphere. The layers respectively  
5      have an exposed outer edge spaced inside of the substrate periphery.  
6      Etching is conducted into the higher oxidation rate material at a faster  
7      rate than any etching which occurs into the lower oxidation rate  
8      material. Then, the substrate is exposed to the oxidizing atmosphere.  
9      In another implementation, a stack of at least two conductive layers for  
10     an electronic component is formed. The two conductive layers have  
11     different oxidation rates when exposed to an oxidizing atmosphere. The  
12     layer with the higher oxidation rate has an outer lateral edge which is  
13     recessed inwardly of a corresponding outer lateral edge of the layer  
14     with the lower oxidation rate. The stack is exposed to the oxidizing  
15     atmosphere effective to grow an oxide layer over the outer lateral edges  
16     of the first and second layers. In yet another implementation, a  
17     transistor comprises a semiconductive substrate and a gate stack formed  
18     thereover. The stack in at least one cross section defines a channel  
19     length within the substrate of less than 1 micron, with the stack  
20     comprising conductive material formed over a gate dielectric layer. An  
21     insulative layer is formed on outer lateral edges of the conductive  
22     material, with such layer having opposing substantially continuous straight  
23     linear outer lateral edges over all conductive material of the gate stack  
24     within the one cross section.